

SANYO

No.1390D

2SA1353/2SC3417

PNP/NPN Epitaxial Planar Silicon Transistors

Ultrahigh-Definition CRT Display

Video Output Applications

Applications

- Ultrahigh-definition CRT display.
- Color TV chroma output, high-voltage driver applications

Features

- High breakdown voltage : $V_{CEO} \geq 300V$.
- Excellent high frequency characteristics : $C_{re} = 1.8pF$ (typ).
- Adoption of MBIT process.

() : 2SA1353

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector-to-Base Voltage	V_{CBO}	(-)300	V
Collector-to-Emitter Voltage	V_{CEO}	(-)300	V
Emitter-to-Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)100	mA
Collector Current (Pulse)	I_{CP}	(-)200	mA
Collector Dissipation	P_C	1.2	W
		7	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

 $T_c = 25^\circ C$ **Electrical Characteristics at $T_a = 25^\circ C$**

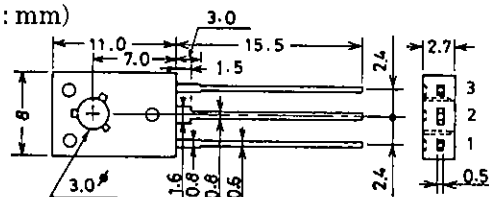
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)200V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)10mA$	40		320	
Gain Bandwidth Product	f_T	$V_{CE} = (-)30V, I_C = (-)10mA$		70		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)300			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)300			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		2.6		pF
				(3.1)		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = (-)30V, f = 1MHz$		1.8		pF
				(2.3)		pF

※ : The 2SA1353/2SC3417 are classified by 10mA h_{FE} as follows :

40	C	80	60	D	120	100	E	200	160	F	320
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Package Dimensions 2009B

(unit : mm)

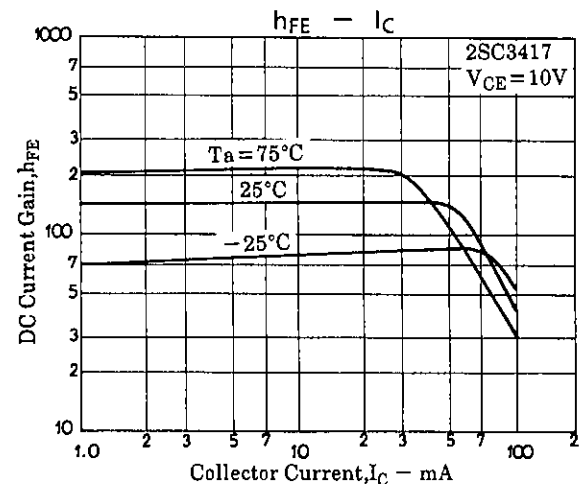
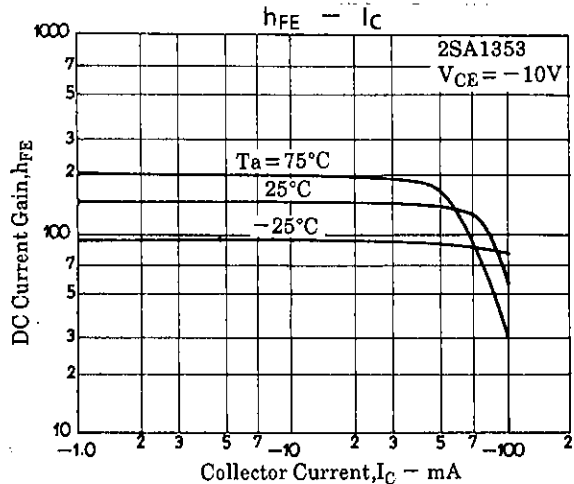
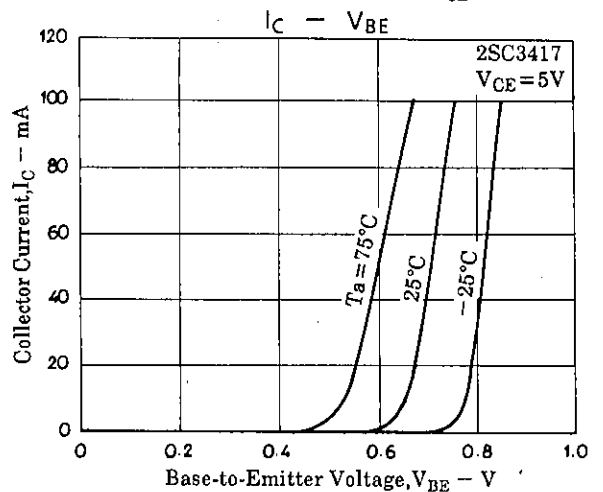
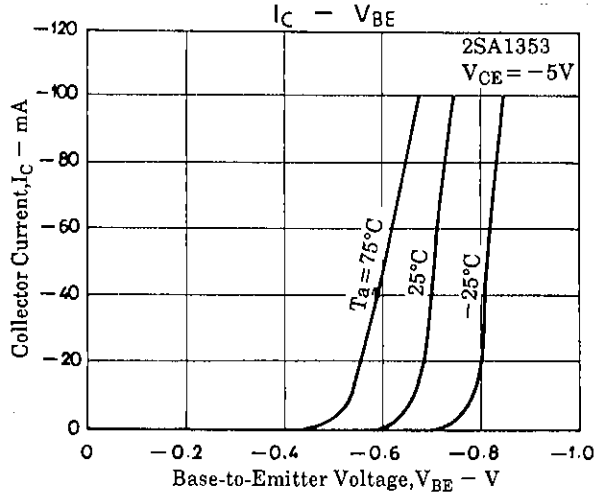
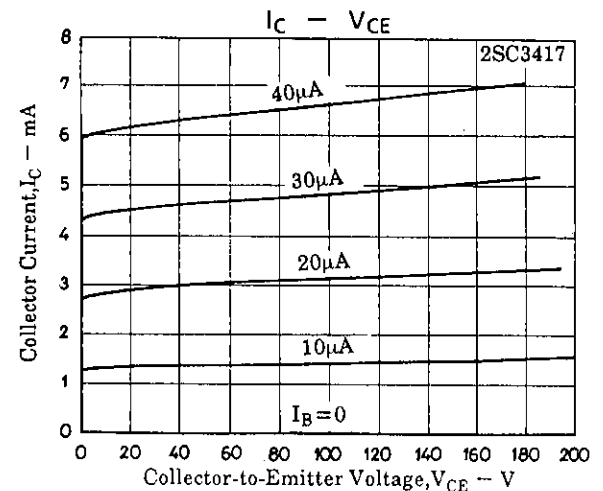
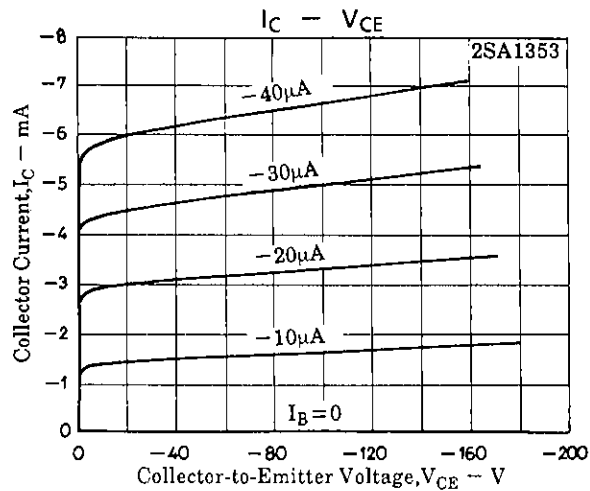
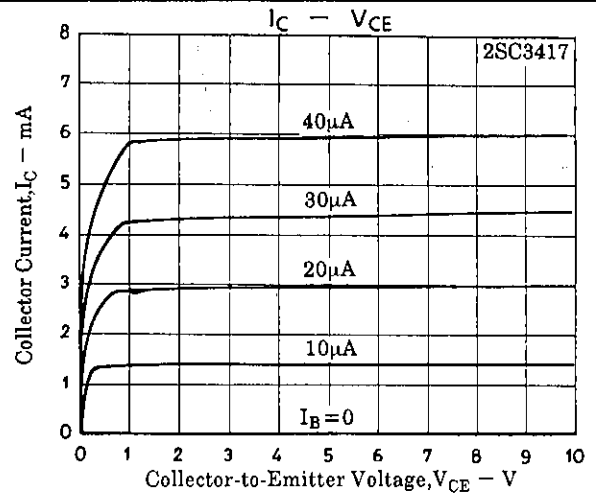
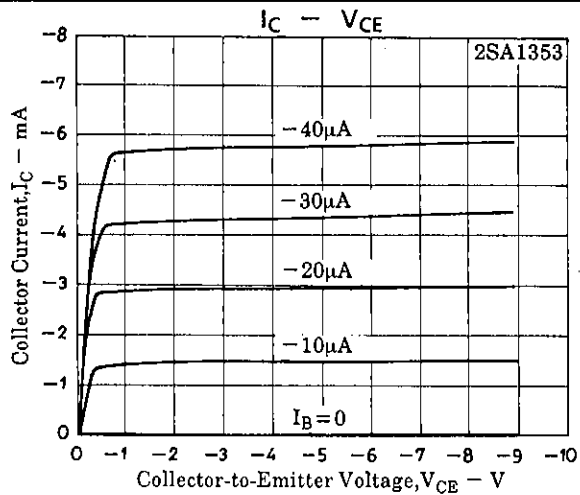


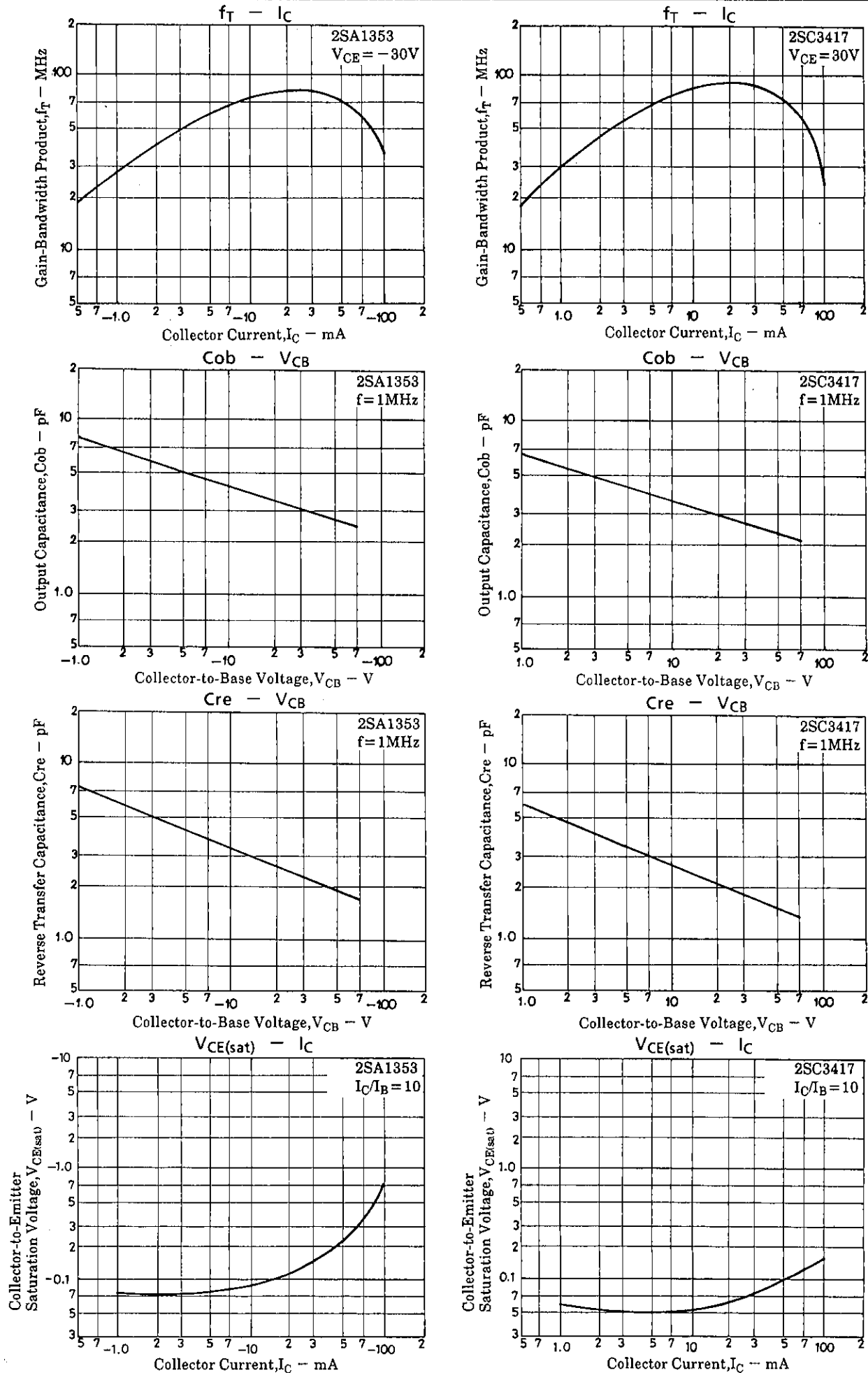
JEDEC: TO-126

1 : Emitter
2 : Collector
3 : Base

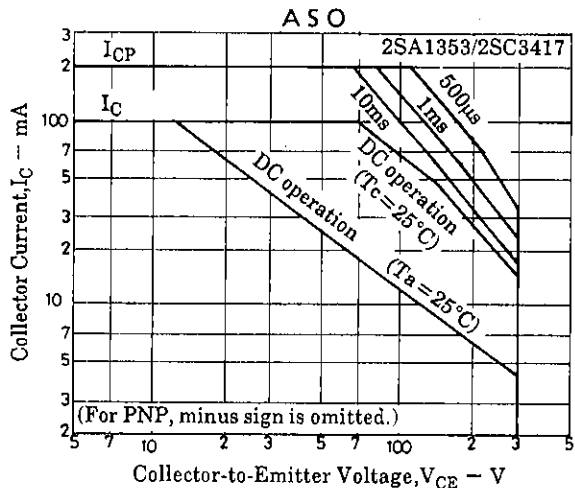
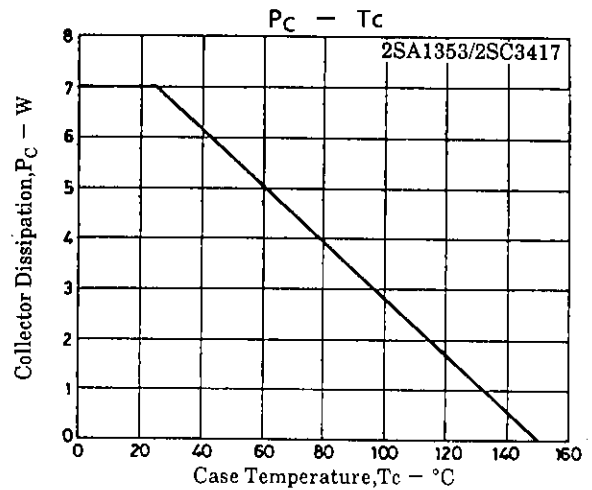
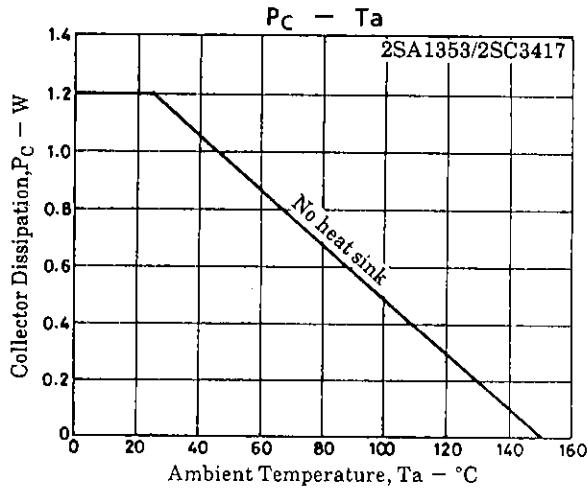
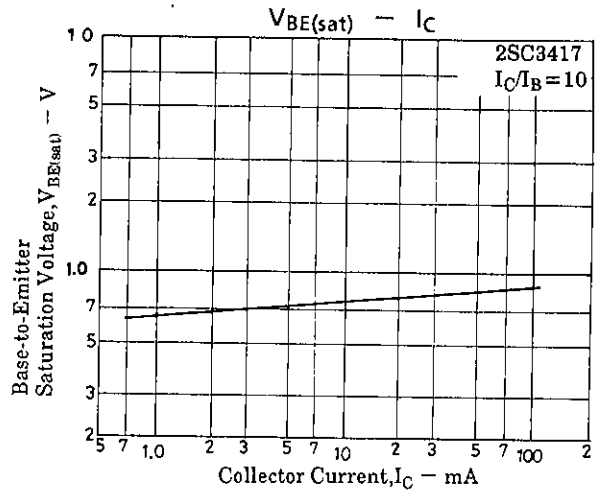
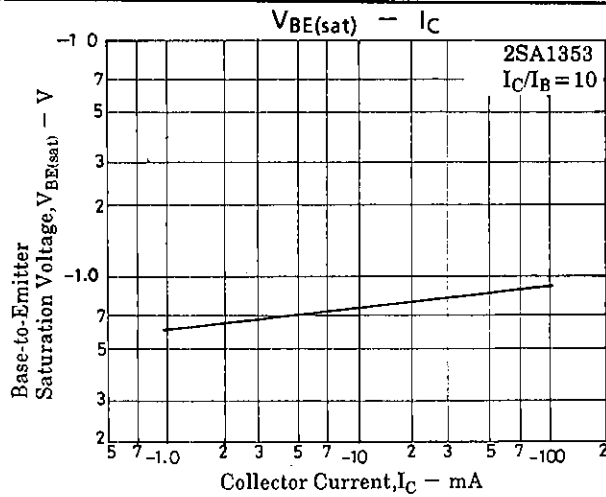
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2SA1353/2SC3417



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